





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

• Case: SOT-523

 Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

 Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208

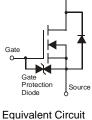
• Terminal Connections: See Diagram

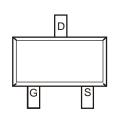
Weight: 0.002 grams (approximate)





SOT-523





Top View Equ

Top View

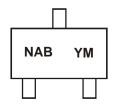
Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2004TK-7	SOT-523	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



NAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	200	6	2007 2008		20	09	2010		2011	2	2012		
Code	Т		U		V		٧	Х		Y		Z	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	N	D	



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 4)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	540 390	mA
Pulsed Drain Current (Note 5)			I _{DM}	1.5	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P_{D}	150	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

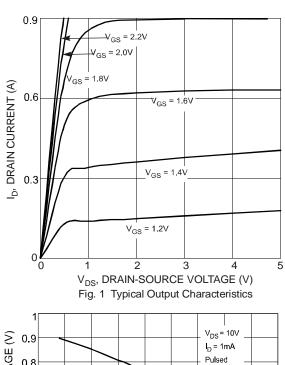
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV_{DSS}	20			V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I	_	8.0	300	nA	$V_{DS} = 16V, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	0.9		nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±1	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	0.5		1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	0.5	0.70	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
	== (=:,)		0.7	0.9		V _{GS} = 1.8V, I _D = 350mA	
Forward Transfer Admittance	Y _{fs}	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage (Note 6)	V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS			_	_			
Input Capacitance	C _{iss}	_	_	150	pF		
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 16V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	_	20	pF	1 = 1.0IVII IZ	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{d(on)}	_	8.5	_	ns	$V_{DD} = 10V, R_L = 47\Omega, I_D = 200 mA,$ $V_{GEN} = 4.5V, R_G = 10\Omega$	
Rise Time	t _r		9.1		ns		
Turn-Off Delay Time	t _{d(off)}	_	51	_	ns		
Fall Time	t _f	_	28	_	ns		

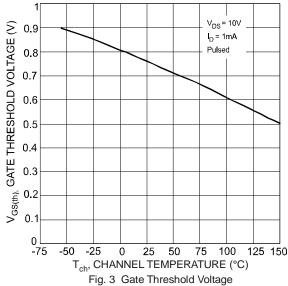
Notes:

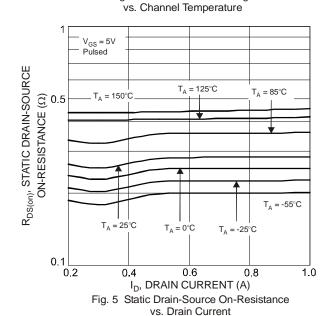
4. Device mounted on FR-4 PCB. 5. Pulse width \leq 10 μ S, Duty Cycle \leq 1%

6. Short duration pulse test used to minimize self-heating effect.









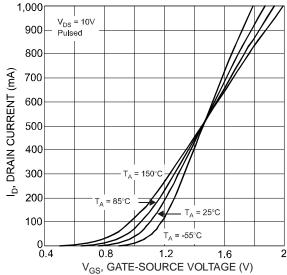


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

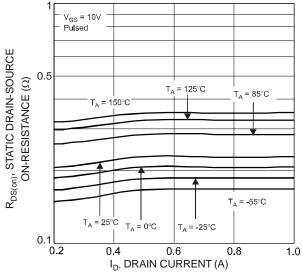


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

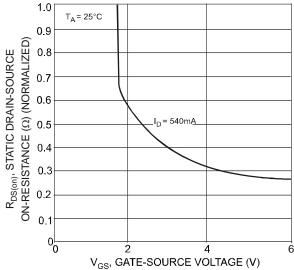


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



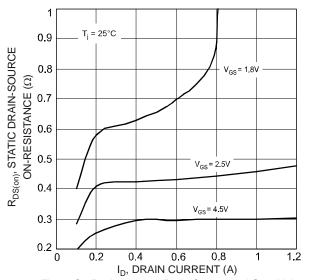
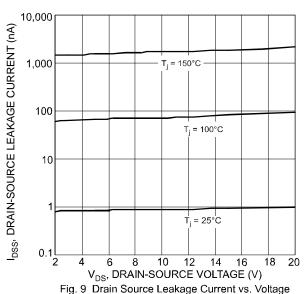


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage



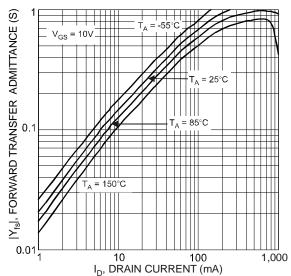


Fig. 11 Forward Transfer Admittance vs. Drain Current

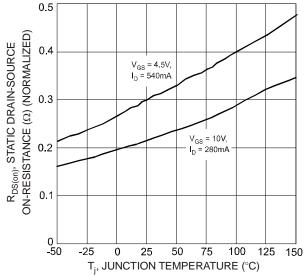


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

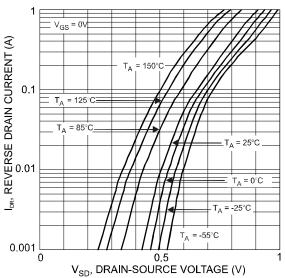
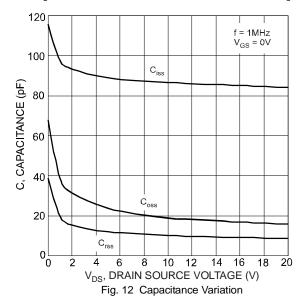
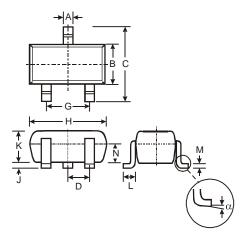


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage



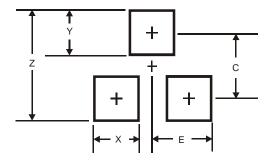


Package Outline Dimensions



SOT-523						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
C	1.45	1.75	1.60			
D	_	_	0.50			
G	0.90	1.10	1.00			
Η	1.50	1.70	1.60			
J	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
М	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°	_			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
X	0.4
Υ	0.51
С	1.3
E	0.7



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2010, Diodes Incorporated

www.diodes.com